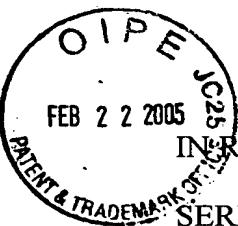


DOCKET NO.: 241473US2/anc



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Hiroaki HAZAMA

SERIAL NUMBER: 10/639,443

GROUP: 2826

FILED: August 13, 2003

EXAMINER: ABRAHAM, FETSUM

FOR: A SEMICONDUCTOR MEMORY DEVICE HAVING A MULTI-LAYERED
INTERPLAYER INSULATION CONSISTING OF DEUTERIUM AND NITRIDE

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE
COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: A SEMICONDUCTOR MEMORY DEVICE HAVING A
MULTI-LAYERED INTERPLAYER INSULATION CONSISTING OF DEUTERIUM
AND NITRIDE.

Respectfully Submitted,

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